NSVG1001MX

Product Preview **RF SPDT Switch MMIC**

This device is single pole dual throw (SPDT) type RF antenna switch MMIC. It has low insertion loss and high isolation. This is designed for wireless communication applications such as WLAN.

It adopts a small surface mount package and it is also suitable for portable devices such as smart phones.

Features

- Low Insertion Loss
- High Isolation
- Middle Power
- Small-sized Package
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- IEEE802.11 a/b/g/n/ac WLAN, Bluetooth[®] Systems
- LTE
- Wireless Communication Applications

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Control Voltage	V _{CTL}	6	V
Power Dissipation	PD	150	mW
Storage Temperature Range	T _{stg}	–55 to +150	°C
Operating Temperature Range	T _{opr}	-40 to +105	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

TRUTH TABLE

On Path	V _{CTL1}	V _{CTL2}	
IN – OUT1	Low	High	
IN – OUT2	High	Low	

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

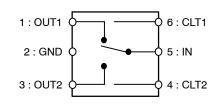


ON Semiconductor®

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1 XDFN6 MX SUFFIX CASE 711AN

ELECTRICAL CONNECTION



MARKING DIAGRAM



A

Μ

ORDERING INFORMATION

Device	Package	Shipping [†]
NSVG1001MXT1G	XDFN6 (Pb–Free)	3000 / Tape & Reel

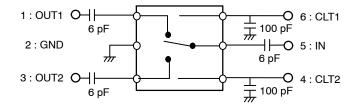
+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSVG1001MX

				Value			
Parameter	Symbol	Path	Condition	Min	Тур	Max	Unit
Insertion Loss	IL	IN to OUT1, OUT2	f = 2.5 GHz		0.37	0.5	dB
			f = 6.0 GHz		0.47	0.65	
Isolation	ISL	IN to OUT1, OUT2	f = 2.5 GHz	25.0	28.0		dB
			f = 6.0 GHz	28.0	33.0		
Return Loss	RL		f = 2.5 GHz		25.0		dB
			f = 6.0 GHz		23.0		
1 dB Loss Compression Input Power	Pin 1 dB	IN to OUT1, OUT2	f = 2.5 GHz		32.0		dBm
			f = 6.0 GHz		32.0		
Switching Time			f = 1GHz to 6GHz		100	250	ns
Switching Control Current	I _{CTL}		No Signal		0.1		μA

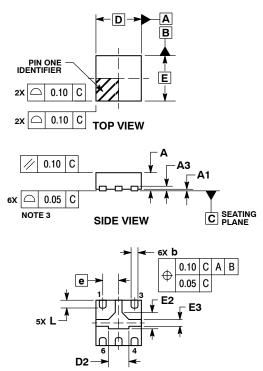
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pay attention to handling since it is liable to be affected by static electricity due to the high-frequency process adopted.

Test Circuit



PACKAGE DIMENSIONS

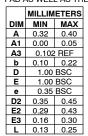
XDFN6 1.0x1.0, 0.35P CASE 711AN ISSUE A



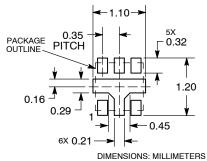
BOTTOM VIEW

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS.
 COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.



RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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